

Smart High-Side Power Switch

Features

- Overload protection
- Current limitation
- Short circuit protection
- Thermal shutdown with restart
- Overvoltage protection (including load dump)
- Fast demagnetization of inductive loads
- Reverse battery protection with external resistor
- Open drain diagnostic output for overtemperature and short circuit
- Open load detection in OFF State with external resistor
- CMOS compatible input
- ullet Loss of GND and loss of $V_{
 m bb}$ protection
- ESD Protection
- Very low standby current
- Green product (RoHS-compliant)

Application

- All types of resistive, inductive and capacitive loads
- μC compatible power switch for 12 V, 24 V and 42 V DC applications
- Replaces electromechanical relays and discrete circuits

General Description

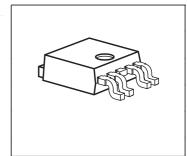
N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS[®] technology. Providing embedded protective functions.

Product Summary

Overvoltage protection	$V_{\rm bb(AZ)}$	62	V
Operating voltage	V _{bb(on)}	652	V
On-state resistance	R _{ON}	200	mΩ
Nominal load current	I _{L(ISO)}	1.8	Α



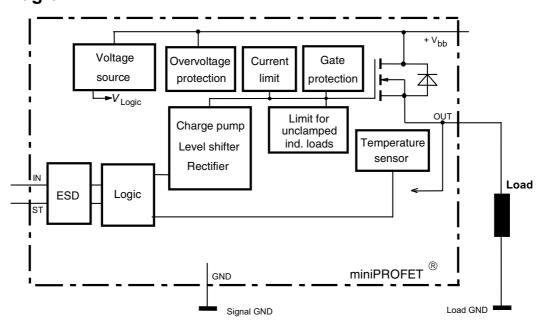




PG-TO252-5-11

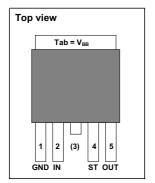


Block Diagram



Pin	Symbol	Function
1	GND	Logic ground
2	IN	Input, activates the power switch in case of logic high signal
3	Vbb	Positive power supply voltage
4	ST	Diagnostic feedback
5	OUT	Output to the load
TAB	Vbb	Positive power supply voltage

Pin configuration





Maximum Ratings at $T_j = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Supply voltage	V _{bb}	52	V
Supply voltage for full short circuit protection	V _{bb(SC)}	50	
Continuous input voltage	V _{IN}	-10 +16	
Load current (Short - circuit current, see page 5)	I _L	self limited	Α
Current through input pin (DC)	I _{IN}	± 5	mA
Operating temperature	Tj	-40+150	°C
Storage temperature	$T_{\rm stg}$	-55 +150	
Power dissipation 1)	P _{tot}	41.6	W
Inductive load switch-off energy dissipation 1)2)	E _{AS}	150	mJ
single pulse, (see page 9)			
Tj =150 °C, <i>I</i> _L = 1 A			
Load dump protection ²⁾ $V_{\text{LoadDump}}^{3} = V_{\text{A}} + V_{\text{S}}$	V _{Loaddump}		V
$R_{\rm I}$ =2 Ω , $t_{\rm d}$ =400ms, $V_{\rm IN}$ = low or high, $V_{\rm A}$ =13.5V			
R_{L} = 13.5 Ω		73.5	
R_{L} = 27 Ω		88.5	
Electrostatic discharge voltage (Human Body Model)	V _{ESD}		kV
according to ANSI EOS/ESD - S5.1 - 1993			
ESD STM5.1 - 1998			
Input pin		± 1	
all other pins		± 5	

Thermal Characteristics

junction - case:	R _{thJC}	-	-	3	K/W
Thermal resistance @ min. footprint	$R_{th(JA)}$	-	80	-	K/W
Thermal resistance @ 6 cm ² cooling area ¹⁾	$R_{th(JA)}$	-	45	60	

 $^{^1}Device$ on $50mm^*50mm^*1.5mm$ epoxy PCB FR4 with 6 cm2 (one layer, $70\mu m$ thick) copper area for drain connection. PCB is vertical without blown air.

²not subject to production test, specified by design

 $^{^3\}emph{V}_{Loaddump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839 .

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND pin, e.g. with a

 $^{150\}Omega$ resistor in GND connection. A resistor for the protection of the input is integrated.



Electrical Characteristics

Parameter and Conditions	Symbol		Values		Unit	
at $T_{\rm j}$ = -40+150°C, $V_{\rm bb}$ = 1242V, unless otherwise specified		min.	typ.	max.		
Load Switching Capabilities and Characteristics						
On-state resistance	R _{ON}				mΩ	
$T_{\rm j}$ = 25 °C, $I_{\rm L}$ = 1 A, $V_{\rm bb}$ = 952 V		-	150	200		
$T_{j} = 150 ^{\circ}\text{C}$		-	270	380		
Nominal load current; Device on PCB 1)	I _{L(ISO)}	1.8	2.2	-	Α	
$T_{\rm C}$ = 85 °C, $V_{\rm ON}$ = 0.5 V						
Turn-on time to 90% V _{OUT}	t_{on}	-	80	180	μs	
R_{L} = 47 Ω						
Turn-off time to 10% V _{OUT}	$t_{\rm off}$	-	80	200		
R_{L} = 47 Ω						
Slew rate on 10 to 30% V _{OUT} ,	dV/dt _{on}	-	0.7	2	V/µs	
$R_{L} = 47 \Omega, V_{bb} = 13.5 V$						
Slew rate off 70 to 40% V _{OUT} ,	-dV/dt _{off}	-	0.9	2	1	
$R_{\rm L}$ = 47 Ω , $V_{\rm bb}$ = 13.5 V						

Operating Parameters

Operating voltage	V _{bb(on)}	6	-	52	V
Undervoltage shutdown of charge pump	V _{bb(under)}				
$T_{j} = -40+85 ^{\circ}\text{C}$,	-	-	4	
T _j = 150 °C		-	-	5.5	
Undervoltage restart of charge pump	V _{bb(u cp)}	-	4	5.5	
Standby current	I _{bb(off)}				μA
$T_{\rm j}$ = -40+85 °C, $V_{\rm IN}$ = low		-	-	15	
$T_{\rm j}$ = +150 °C ²⁾ , $V_{\rm IN}$ = low		-	-	18	
Leakage output current (included in Ibb(off))	I _{L(off)}	-	-	5	
$V_{\text{IN}} = \text{low}$, ,				
Operating current	I _{GND}	_	0.8	2	mA
V_{IN} = high					

¹Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70μm thick) copper area for drain connection. PCB is vertical without blown air.

²higher current due temperature sensor



Electrical Characteristics

Parameter and Conditions	Symbol		Values		Unit
at T_i = -40+150°C, V_{bb} = 1242V, unless otherwise specified		min.	typ.	max.	
Protection Functions ¹⁾	•				•
Initial peak short circuit current limit (pin 3 to 5)	I _{L(SCp)}				Α
$T_{\rm j}$ = -40 °C, $V_{\rm bb}$ = 20 V, $t_{\rm m}$ = 150 $\mu {\rm s}$		-	-	9	
T _j = 25 °C		-	6.5	-	
T _j = 150 °C		4	-	-	
$T_{\rm j}$ = -40+150 °C, $V_{\rm bb}$ > 40 V, (see page 12)		-	52)	-	
Repetitive short circuit current limit	I _{L(SCr)}				
T _j = T _{jt} (see timing diagrams)					
V _{bb} < 40V		-	6	-	
V _{bb} > 40V		-	4.5	-	
Output clamp (inductive load switch off)	V _{ON(CL)}	59	63	-	V
at $V_{\text{OUT}} = V_{\text{bb}} - V_{\text{ON(CL)}}$,					
$I_{\rm bb} = 4 \text{ mA}$					
Overvoltage protection 3)	V _{bb(AZ)}	62	-	-	
$I_{\rm bb} = 4 \text{ mA}$,				
Thermal overload trip temperature	T _{it}	150	-	-	°C
Thermal hysteresis	$\Delta T_{\rm jt}$	-	10	-	K
					-
Reverse Battery	T		T		T.,
Reverse battery ⁴⁾	-V _{bb}	-	-	52	V

Drain-source diode voltage ($V_{OUT} > V_{bb}$)

 $T_{\rm i}$ = 150 °C

 $-V_{ON}$

600

mV

¹Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

²not subject to production test, specified by design

³ see also V_{ON(CL)} in circuit diagram on page 8

 $^{^4}$ Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input current has to be limited (see max. ratings page 3).



Electrical Characteristics

Parameter and Conditions	Symbol		Values		Unit
at T_i = -40+150°C, V_{bb} = 1242V, unless otherwise specified		min.	typ.	max.	
Input and Status feedback	•				
Input turn-on threshold voltage	$V_{IN(T+)}$	-	-	2.2	V
Input turn-off threshold voltage	$V_{IN(T-)}$	8.0	-	-	
Input threshold hysteresis	$\Delta V_{\rm IN(T)}$	-	0.4	-	
Off state input current	I _{IN(off)}	1	-	25	μA
$V_{IN} = 0.7 \text{ V}$					
On state input current	I _{IN(on)}	3	-	25	
_V _{IN} = 5 V					
Status output (open drain), Zener limit voltage	V _{ST(high)}	5.4	6.1	-	V
I _{ST} = 1.6 mA					
Status output (open drain), ST low voltage	V _{ST(low)}				
$T_{\rm j}$ = -40+25 °C, $I_{\rm ST}$ = 1.6 mA		-	-	0.4	
$T_{\rm j}$ = 150 °C, $I_{\rm ST}$ = 1.6 mA		-	-	0.6	
Status invalid after positive input slope 1)	$t_{d(ST+)}$	-	120	160	μs
$V_{\rm bb}$ = 20 V					
Status invalid after negative input slope 1)	t _{d(ST-)}	-	250	400	
Input resistance (see page 8)	R_{I}	2	3.5	5	kΩ

Diagnostic Characteristics

Short circuit detection voltage	V _{OUT(SC)}	ı	2.8	ı	V
Open load detection voltage ²⁾	V _{OUT(OL)}	ı	3	4	
Internal output pull down ³⁾	R _O	65	200	750	kΩ
(see page 9 and 14)					
$V_{OUT(OL)} = 4 \text{ V}$					

¹no delay time after overtemperature switch off and short circuit in on-state

 $^{^2\}mbox{External}$ pull up resistor required for open load detection in off state.

³not subject to production test, specified by design



	Input	Output	Status
	level	level	
Normal	L	L	Н
operation	Н	Н	Н
Short circuit	L	L	Н
to GND	Н	L *	L
Short circuit to	L	Н	L
V _{bb} (in off-state)	Н	Н	Н
Overload	L	L	Н
	Н	H **	Н
Overtemperature	L	L	Н
	Н	L	L
Open Load in	L	Z	H (L ¹⁾)
off-state	Н	Н	н

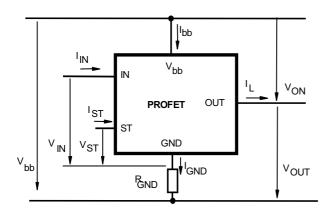
^{*)} Out ="L": V_{OUT} < 2.8V typ.

^{**)} Out ="H": $V_{OUT} > 2.8V \text{ typ.}$

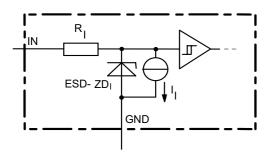
Z = high impedance, potential depends on external circuit



Terms

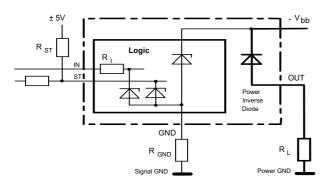


Input circuit (ESD protection)



The use of ESD zener diodes as voltage clamp at DC conditions is not recommended

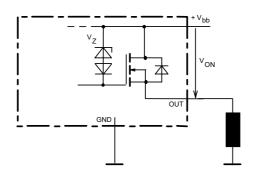
Reverse battery protection



 R_{GND} =150Ω, R_{I} =3.5kΩ typ.,

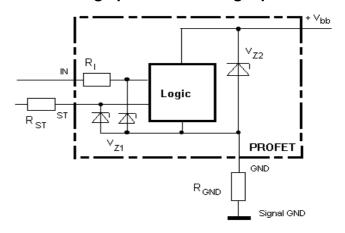
Temperature protection is not active during inverse current

Inductive and overvoltage output clamp



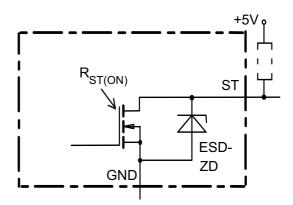
VON clamped to 59V min.

Overvoltage protection of logic part



 V_{Z1} =6.1V typ., V_{Z2} = $V_{bb(AZ)}$ =62V min., R_I=3.5 k Ω typ., R_{GND} =150 Ω

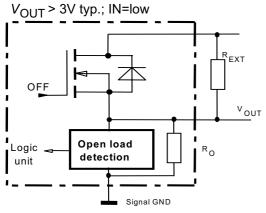
Status output



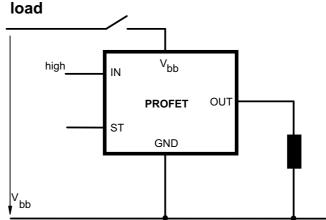


Open-load detection

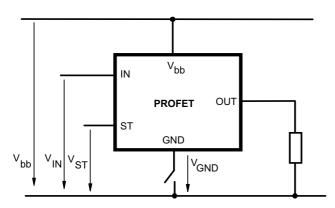
OFF-state diagnostic condition:



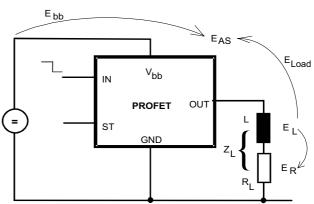
V_{bb} disconnect with charged inductive



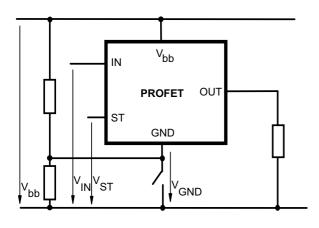
GND disconnect



Inductive Load switch-off energy dissipation



GND disconnect with GND pull up



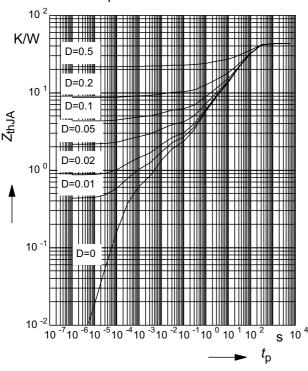
Energy stored in load inductance: $E_L = \frac{1}{2} * L * I_L^2$ While demagnetizing load inductance, the energy dissipated in PROFET is $E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} * i_L(t) dt$, with an approximate solution for $R_L > 0\Omega$:

$$E_{AS} = \frac{I_L * L}{2 * R_L} * (V_{bb} + |V_{OUT(CL)|}) * \ln(1 + \frac{I_L * R_L}{|V_{OUT(CL)}|})$$



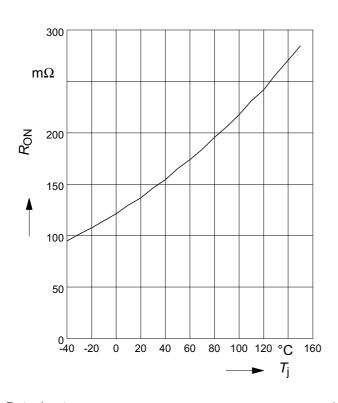
Typ. transient thermal impedance Z_{thJA} =f(t_{p}) @ 6cm² heatsink area

Parameter: $D=t_p/T$



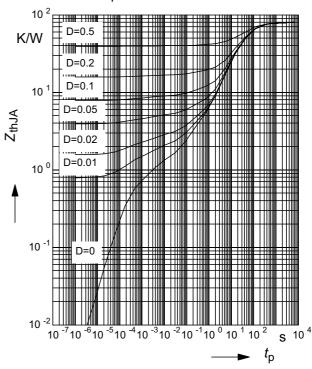
Typ. on-state resistance

$$R_{ON} = f(T_j)$$
; $V_{bb} = 13.5V$; $V_{in} = high$



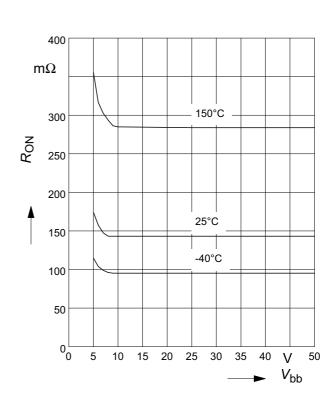
Typ. transient thermal impedance Z_{thJA} =f(t_{p}) @ min. footprint

Parameter: $D=t_p/T$



Typ. on-state resistance

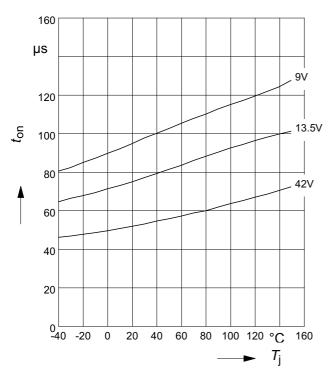
$$R_{ON} = f(V_{bb}); I_L = 1 \text{ A}; V_{in} = \text{high}$$



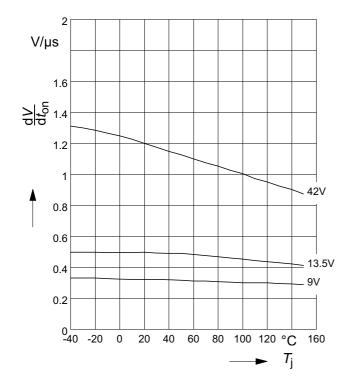


Typ. turn on time

$$t_{on} = f(T_j); R_L = 47\Omega$$

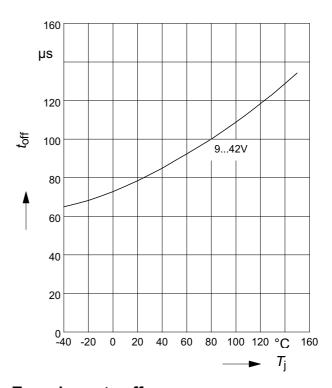


Typ. slew rate on $dV/dt_{on} = f(T_j)$; $R_L = 47 \Omega$

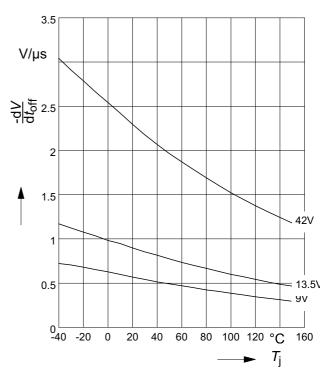


Typ. turn off time

$$t_{\text{off}} = f(T_i)$$
; $R_L = 47\Omega$



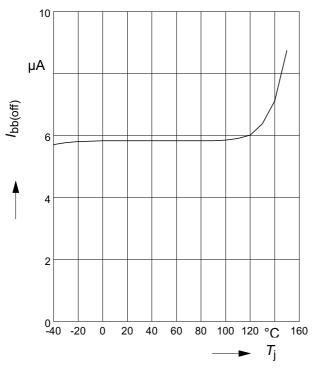
Typ. slew rate off $dV/dt_{off} = f(T_j)$; $R_L = 47 \Omega$



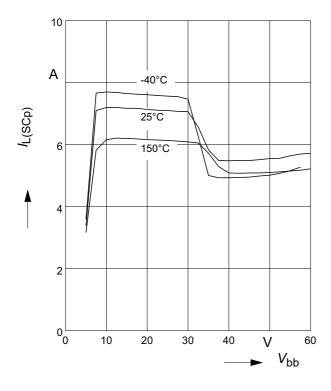


Typ. standby current

$$I_{bb(off)} = f(T_j)$$
; $V_{bb} = 42V$; $V_{IN} = low$

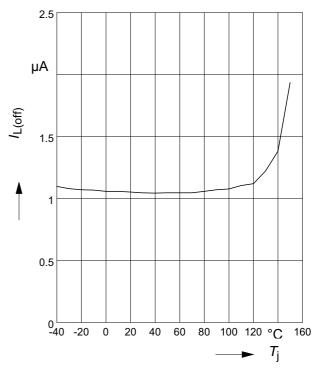


Typ. initial peak short circuit current limit $I_{L(SCp)} = f(V_{bb})$



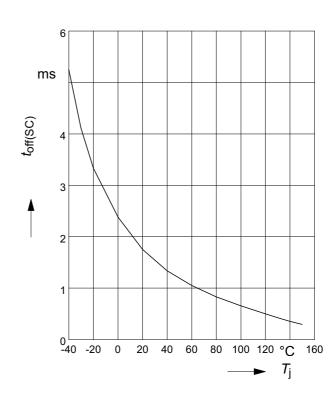
Typ. leakage current

$$I_{L(off)} = f(T_j)$$
; $V_{bb} = 42V$; $V_{IN} = low$



Typ. initial short circuit shutdown time

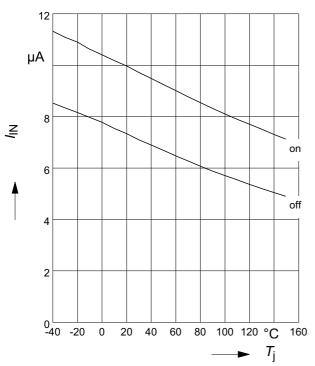
$$t_{\text{off(SC)}} = f(T_{j,\text{start}})$$
; $V_{\text{bb}} = 20V$





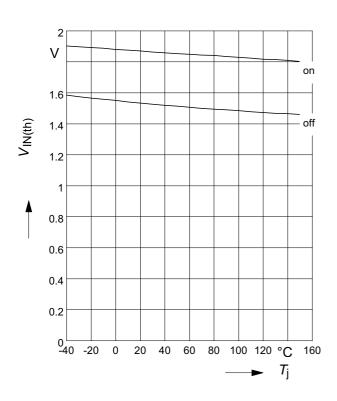
Typ. input current

 $I_{\text{IN(on/off)}} = f(T_j); V_{\text{bb}} = 13.5 \text{V}; V_{\text{IN}} = \text{low/high}$ $V_{\text{INlow}} \le 0.7 \text{V}; V_{\text{INhigh}} = 5 \text{V}$



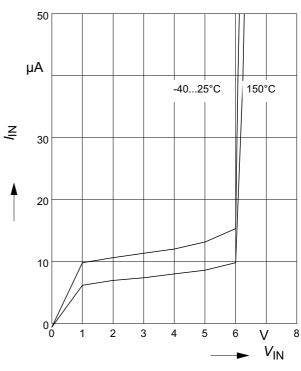
Typ. input threshold voltage

 $V_{\text{IN(th)}} = f(T_{\text{i}})$; $V_{\text{bb}} = 13.5 \text{V}$



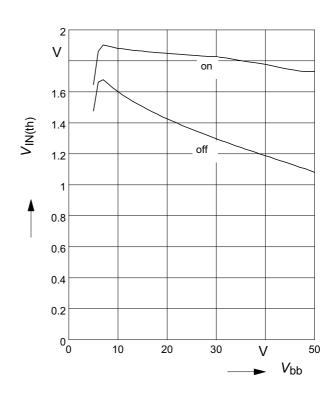
Typ. input current

 $I_{IN} = f(V_{IN}); V_{bb} = 13.5V$



Typ. input threshold voltage

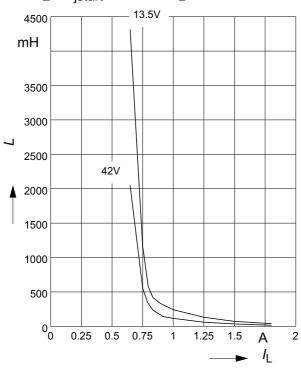
 $V_{IN(th)} = f(V_{bb})$; $T_{j} = 25^{\circ}C$





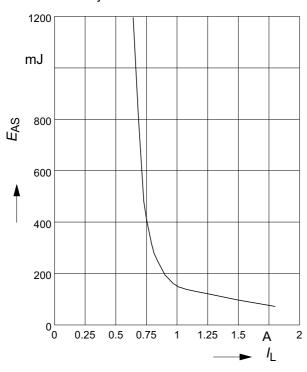
Maximum allowable load inductance for a single switch off

$$\boldsymbol{L}$$
 = f(I_L); T_{jstart} =150°C, R_L =0 Ω



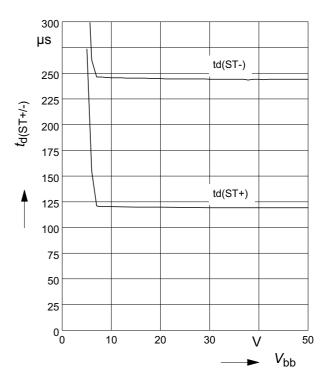
Maximum allowable inductive switch-off energy, single pulse

$$E_{AS} = f(I_L); T_{jstart} = 150$$
°C, $V_{bb} = 13.5$ V

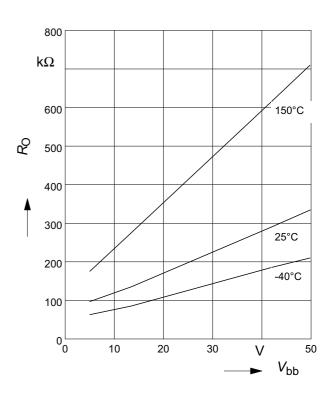


Typ. status delay time

$$t_{d(ST+/-)} = f(V_{bb}); T_j = 25^{\circ}C$$



Typ. internal output pull down $R_{O} = f(V_{bb})$





Timing diagrams

Figure 1a: Vbb turn on:

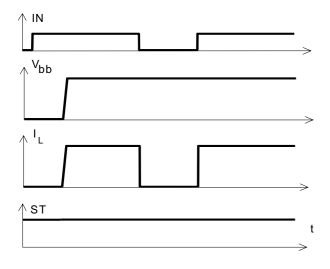


Figure 2b: Switching a lamp,

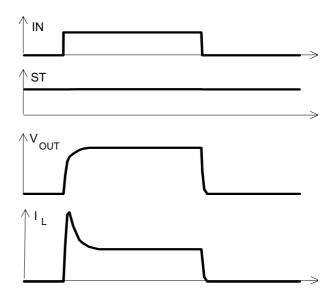


Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition

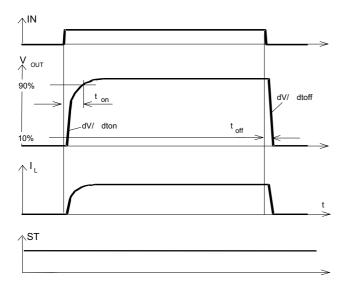


Figure 2c: Switching an inductive load

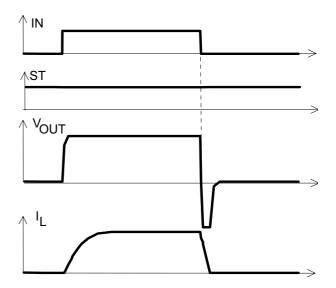
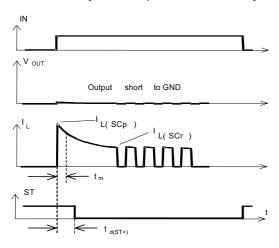




Figure 3a: Turn on into short circuit, shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions.

Figure 4: Overtemperature: Reset if T_i < T_{it}

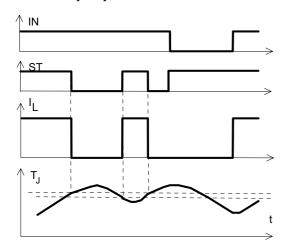


Figure 3b: Short circuit in on-state shut down by overtemperature, restart by cooling

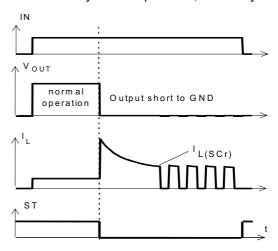


Figure 5: Undervoltage restart of charge pump

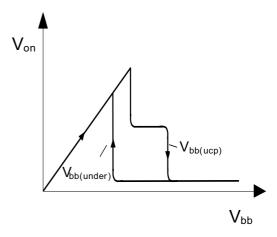
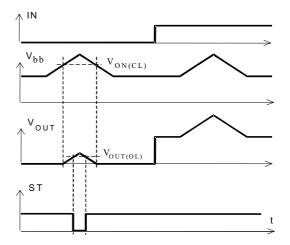


Figure 7: Overvoltage





Package Outlines

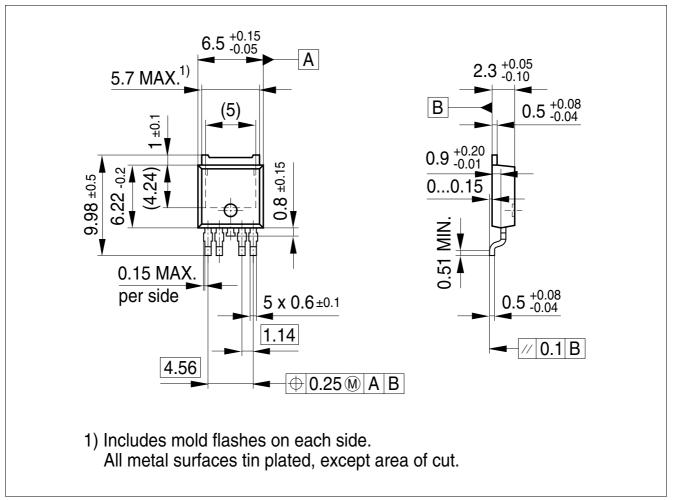


Figure 1 PG-TO252-5-11 (Plastic Dual Small Outline Package) (RoHS-compliant)

Green Product

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Please specify the package needed (e.g. green package) when placing an order.

You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.

Dimensions in mm



Revision History

Version	Date	Changes
V1.0	2004-01-27	initial version
V1.1	2007-01-15	AEC icon added
		RoHS icon added
		Green product (RoHS-compliant) added to the feature list
		Package information updated to green
		Green explanation added

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Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

单击下面可查看定价,库存,交付和生命周期等信息

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